

High-Frequency Amplifier Transistor (11V, 50mA, 3.2GHz)

**2SC5662 / 2SC4726 / 2SC4083 /
2SC3838K / 2SC4043S**

●Features

- 1) High transition frequency. (Typ. $f_r = 1.5\text{GHz}$)
- 2) Small $r_{bb} \cdot C_c$ and high gain. (Typ. 4ps)
- 3) Small NF.

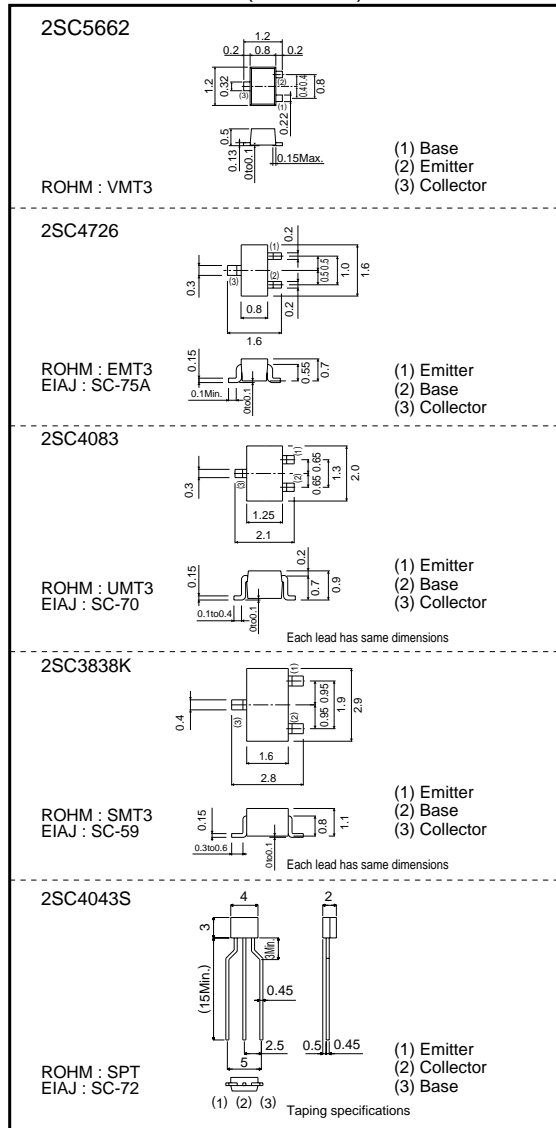
●Absolute maximum ratings ($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Limits	Unit
Collector-base voltage	V_{CBO}	20	V
Collector-emitter voltage	V_{CE0}	11	V
Emitter-base voltage	V_{EB0}	3	V
Collector current	I_C	50	mA
Collector power dissipation	P_C	0.15	W
		0.2	
		0.3	
Junction temperature	T_J	150	$^\circ\text{C}$
Storage temperature	T_{stg}	-55~+150	$^\circ\text{C}$

●Packaging specifications and h_{FE}

Type	2SC5662	2SC4726	2SC4083	2SC3838K	2SC4043S
Package	VMT3	EMT3	UMT3	SMT3	SPT
h_{FE}	NP	NP	NP	NP	P
Marking	AD	AD	1D	AD	-
Code	T2L	TL	T106	T146	TP
Basic ordering unit (pieces)	8000	3000	3000	3000	5000

●External dimensions (Units : mm)



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Transistors

● Absolute maximum ratings (Ta=25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions	
Collector-base breakdown voltage	BV _{CB0}	20	–	–	V	I _c = 10μA	
Collector-emitter breakdown voltage	BV _{CE0}	11	–	–	V	I _c = 1mA	
Emitter-base breakdown voltage	BV _{EB0}	3	–	–	V	I _E = 10μA	
Collector cutoff current	I _{CB0}	–	–	0.5	μA	V _{CB} = 10V	
Emitter cutoff current	I _{EB0}	–	–	0.5	μA	V _{EB} = 2V	
Collector-emitter saturation voltage	V _{CE(sat)}	–	–	0.5	V	I _c /I _E = 10mA/5mA	
DC current transfer ratio	2SC5662, 2SC4726, 2SC4083, 2SC3838K	h _{FE}	56	–	180	–	V _{CE} /I _c = 10V/5mA
	2SC4043S		82	–	180		
Transition frequency	f _T	1.4	3.2	–	GHz	V _{CE} = 10V, I _E = 10mA, f = 500MHz	
Output capacitance	C _{ob}	–	0.8	1.5	pF	V _{CB} = 10V, I _E = 0A, f = 1MHz	
Collector-base time constant	τ _{cb} -C _c	–	4	12	ps	V _{CB} = 10V, I _c = 10mA, f = 31.8MHz	
Noise factor	NF	–	3.5	–	dB	V _{CE} = 6V, I _c = 2mA, f = 500MHz, R _g = 50Ω	